



General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

Applications

- DC/DC Converters in Computing
- POL in Telecom and Industrial

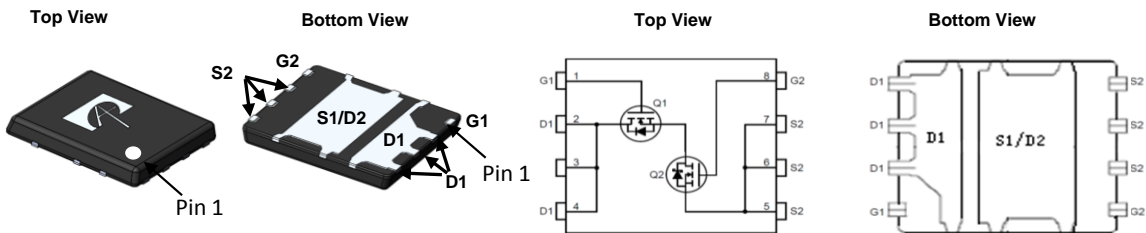
Product Summary

	Q1	Q2
V_{DS}	30V	30V
I_D (at $V_{GS}=10V$)	49A	85A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	<5.3m Ω	<2m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<9.1m Ω	<2.5m Ω

100% UIS Tested
100% Rg Tested



DFN 5X6D



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONY36352	DFN 5x6D	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max Q1	Max Q2	Units	
Drain-Source Voltage	V_{DS}	30	30	V	
Gate-Source Voltage	V_{GS}	± 20	± 12	V	
Continuous Drain Current	I_D	49	85 ^G	A	
Current		$T_C=100^\circ\text{C}$	31		72.5
Pulsed Drain Current ^C	I_{DM}	100	235	A	
Continuous Drain Current	I_{DSM}	18.5	30	A	
Current		$T_A=70^\circ\text{C}$	15		24
Avalanche Current ^C	I_{AS}	50	80	A	
Avalanche energy $L=0.01\text{mH}$ ^C	E_{AS}	13	32	mJ	
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	21	45	W
		$T_C=100^\circ\text{C}$	8.5	18	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	3.1	3.1	W
		$T_A=70^\circ\text{C}$	2	2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$	

Thermal Characteristics

Parameter	Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient ^A $t \leq 10\text{s}$	$R_{\theta JA}$	30	30	40	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D} Steady-State		50	50	65	65	$^\circ\text{C/W}$
Maximum Junction-to-Case Steady-State	$R_{\theta JC}$	4.6	2.2	6	2.8	$^\circ\text{C/W}$

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.3	1.7	2.1	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		4.4	5.3	mΩ
		V _{GS} =4.5V, I _D =20A		6.7	8.1	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		53		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				30	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		820		pF
C _{oss}	Output Capacitance			230		pF
C _{rss}	Reverse Transfer Capacitance			35		pF
R _g	Gate resistance	f=1MHz	0.9	1.8	2.7	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		11	20	nC
Q _g (4.5V)	Total Gate Charge			5	10	
Q _{gs}	Gate Source Charge			2.6		
Q _{gd}	Gate Drain Charge			1.5		
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		6		ns
t _r	Turn-On Rise Time			4		
t _{D(off)}	Turn-Off DelayTime			18		
t _f	Turn-Off Fall Time			2.5		
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		9.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		12.5		nC

- A. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

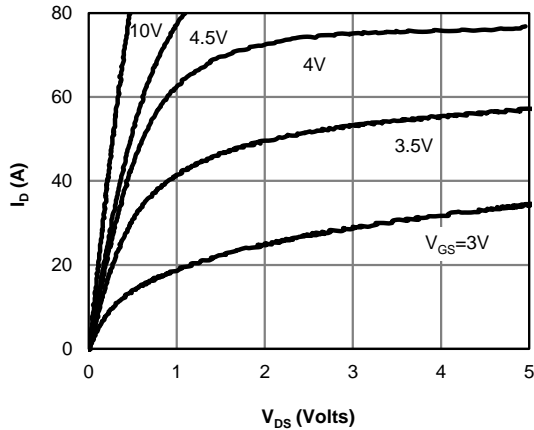


Figure 1: On-Region Characteristics (Note E)

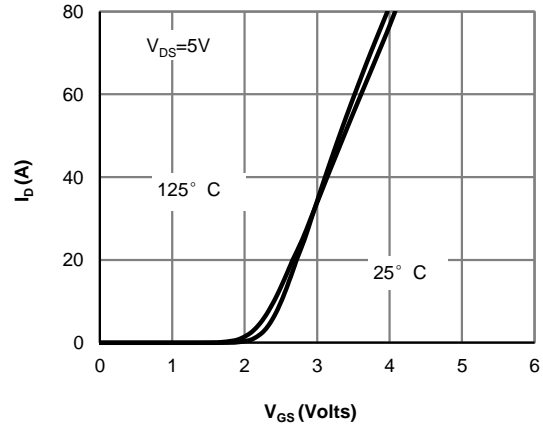


Figure 2: Transfer Characteristics (Note E)

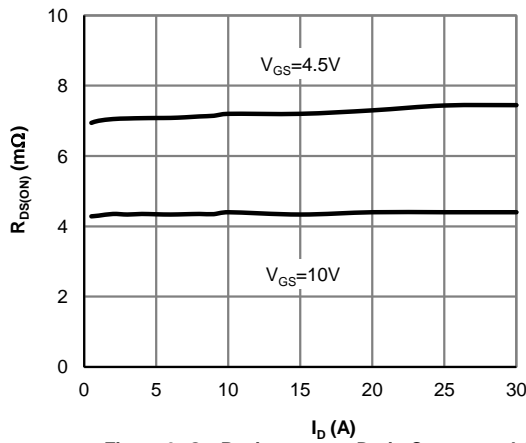


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

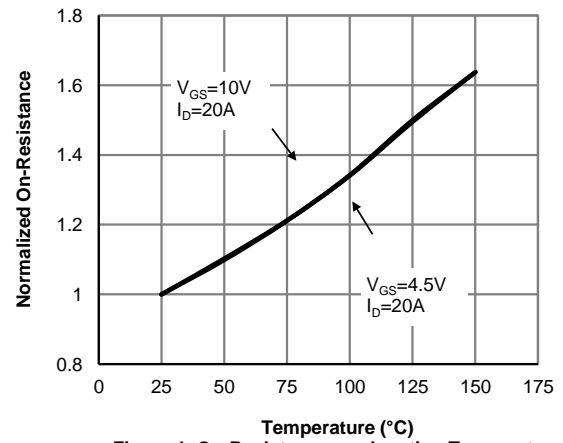


Figure 4: On-Resistance vs. Junction Temperature (Note E)

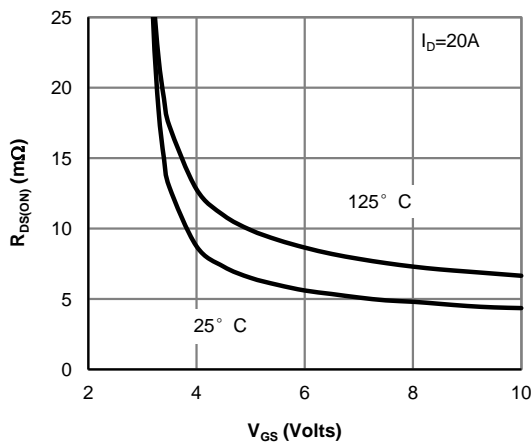


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

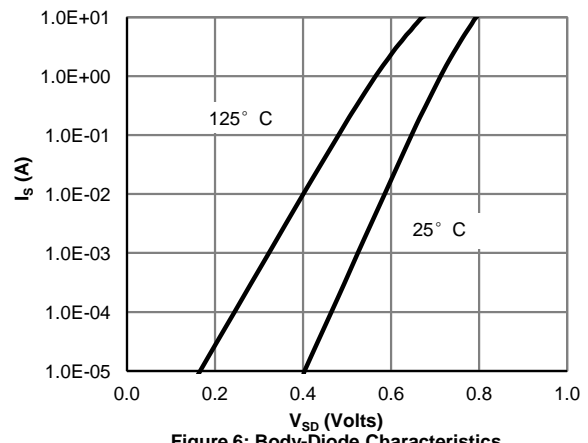


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

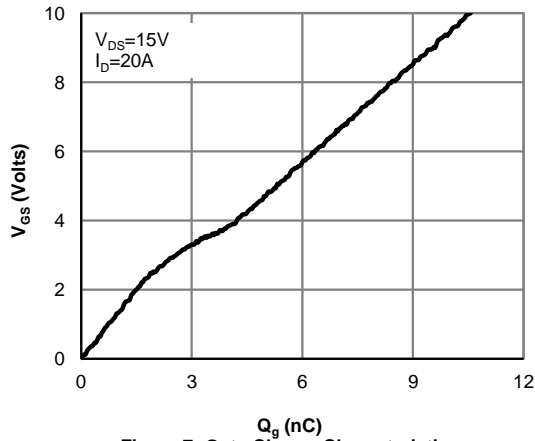


Figure 7: Gate-Charge Characteristics

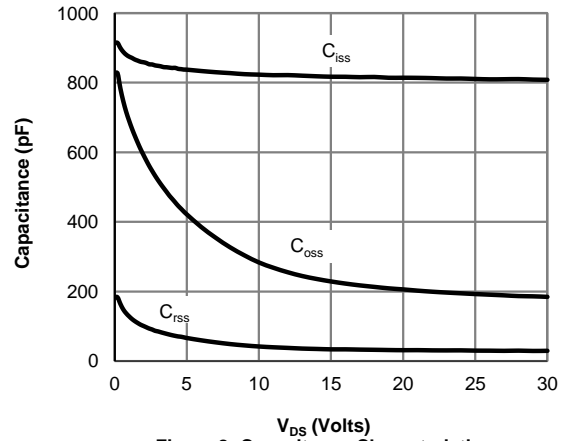


Figure 8: Capacitance Characteristics

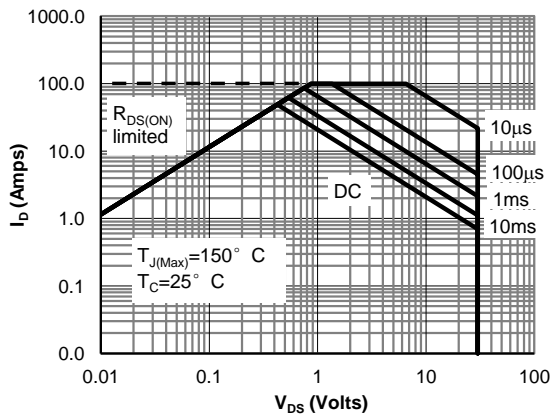


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

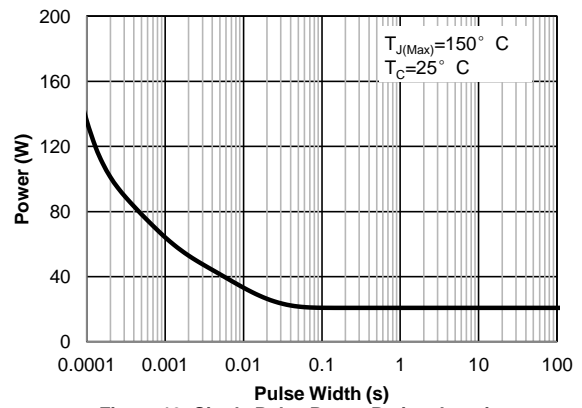


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

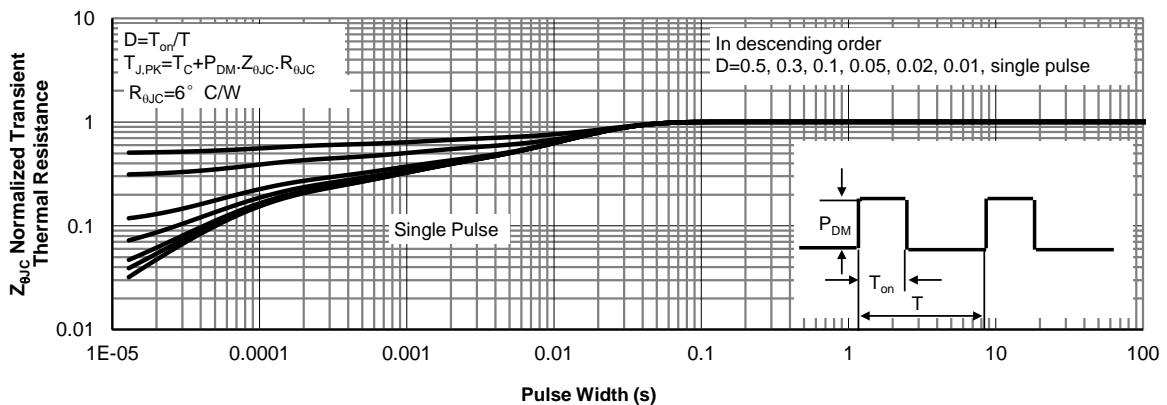


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

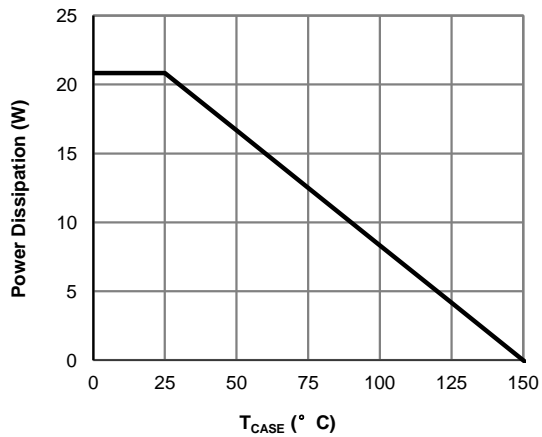


Figure 12: Power De-rating (Note F)

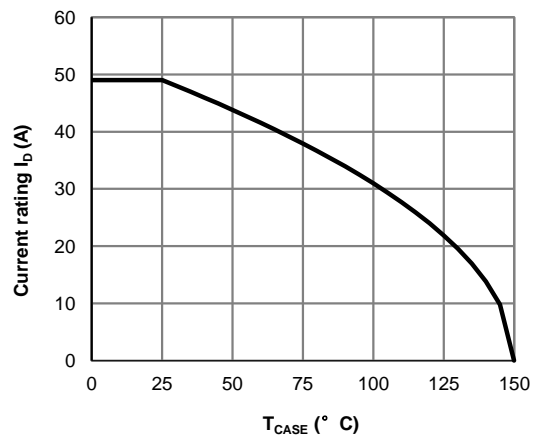


Figure 13: Current De-rating (Note F)

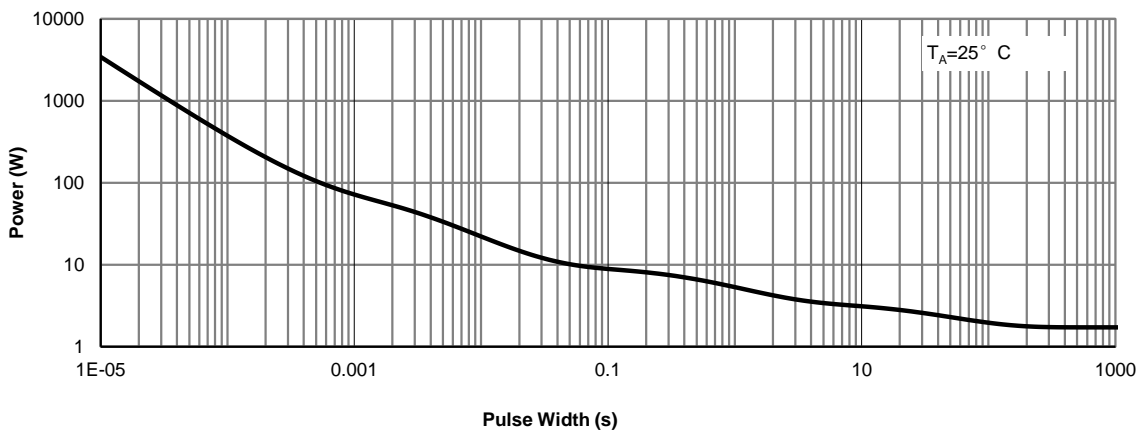


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

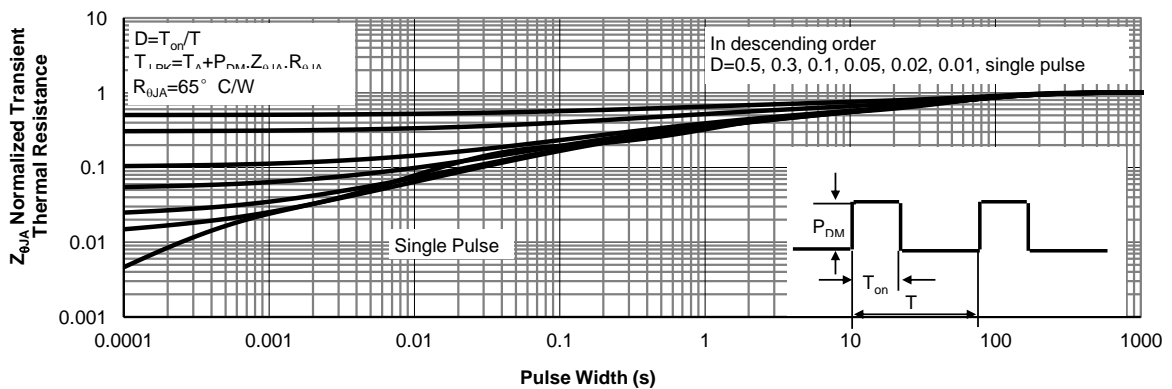


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.1	1.5	1.9	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		1.67	2	mΩ
		V _{GS} =4.5V, I _D =20A		2	2.5	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		165		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				50	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		2555		pF
C _{oss}	Output Capacitance			520		pF
C _{riss}	Reverse Transfer Capacitance			75		pF
R _g	Gate resistance	f=1MHz	1.2	2.4	3.6	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		37	52	nC
Q _{g(4.5V)}	Total Gate Charge			16	25	
Q _{gs}	Gate Source Charge			8		
Q _{gd}	Gate Drain Charge			3		
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		9		ns
t _r	Turn-On Rise Time			4		
t _{D(off)}	Turn-Off Delay Time			38		
t _f	Turn-Off Fall Time			6		
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		14		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		26.5		nC

A. The value of R_{thJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{thJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{thJA} is the sum of the thermal impedance from junction to case R_{thJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

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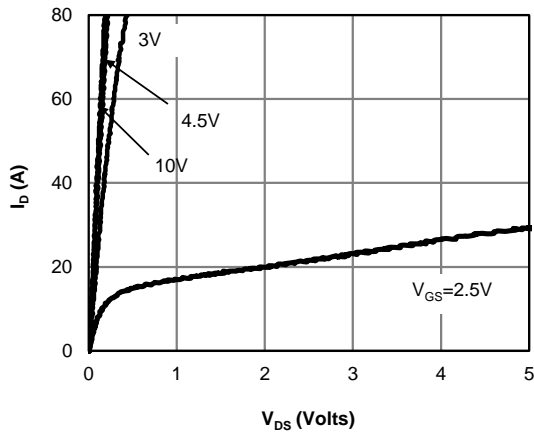


Figure 1: On-Region Characteristics (Note E)

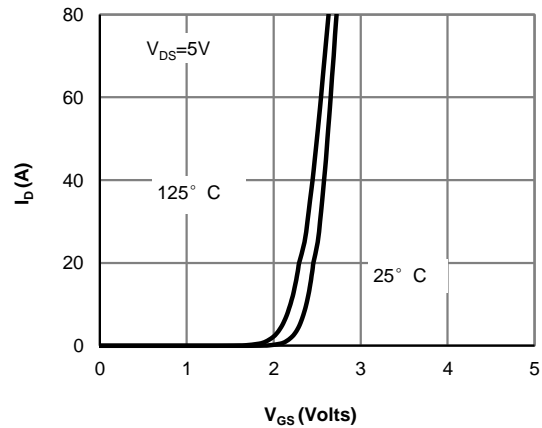


Figure 2: Transfer Characteristics (Note E)

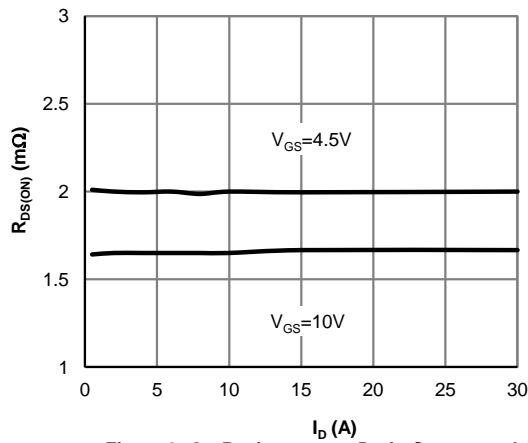


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

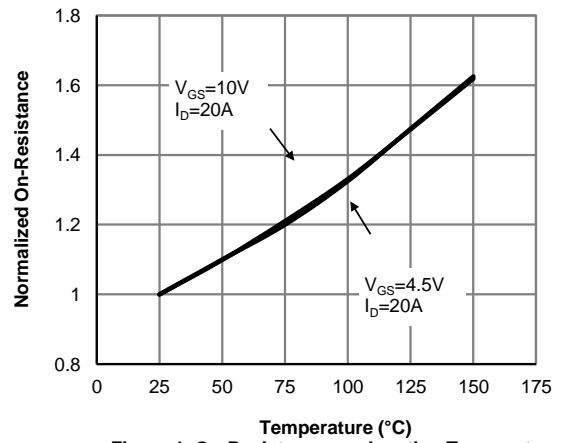


Figure 4: On-Resistance vs. Junction Temperature (Note E)

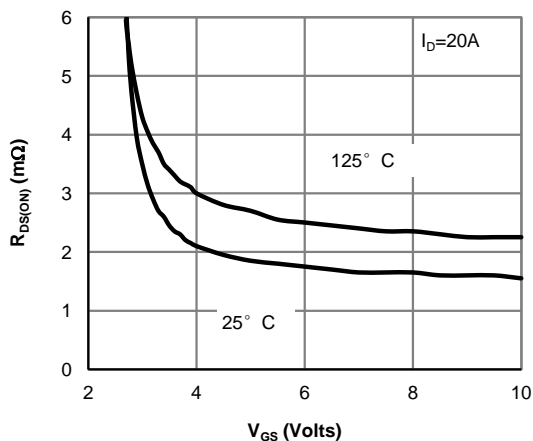


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

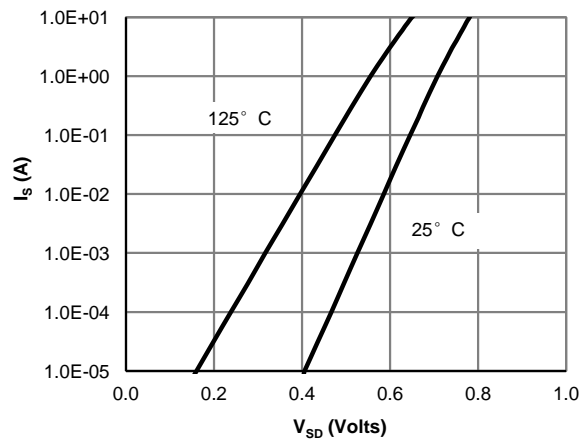


Figure 6: Body-Diode Characteristics (Note E)

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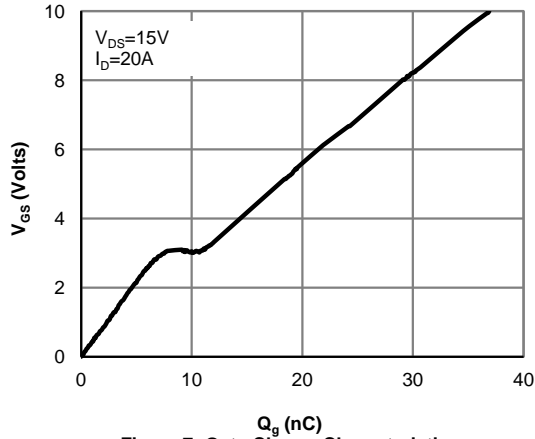


Figure 7: Gate-Charge Characteristics

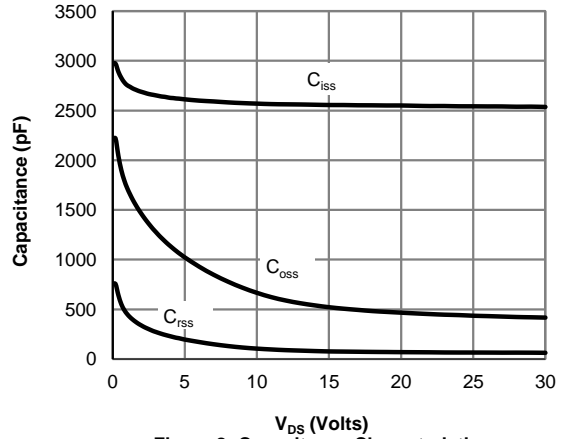


Figure 8: Capacitance Characteristics

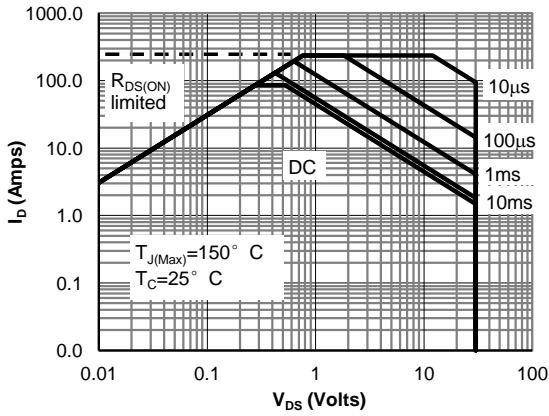


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

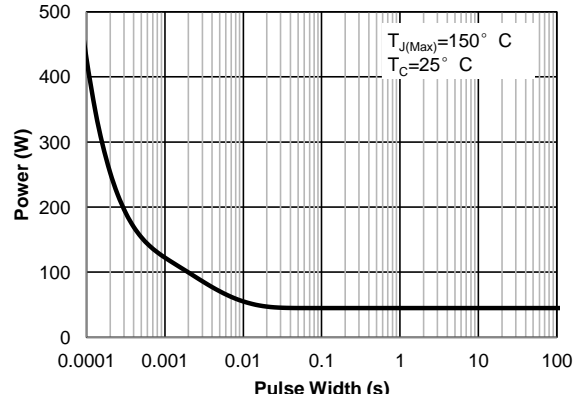


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

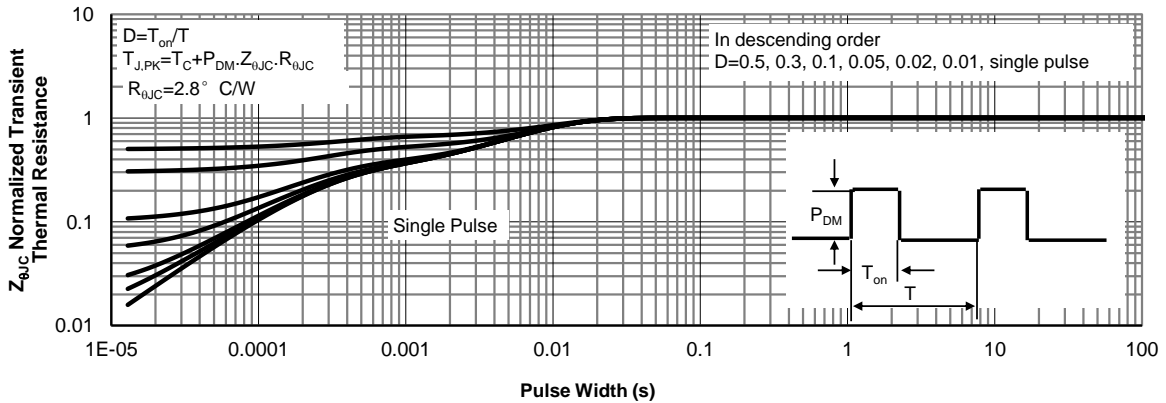


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

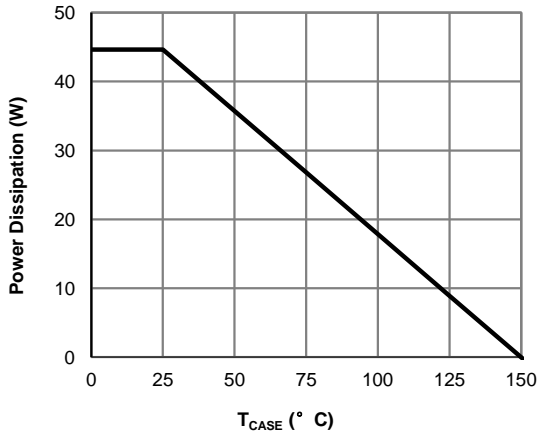


Figure 12: Power De-rating (Note F)

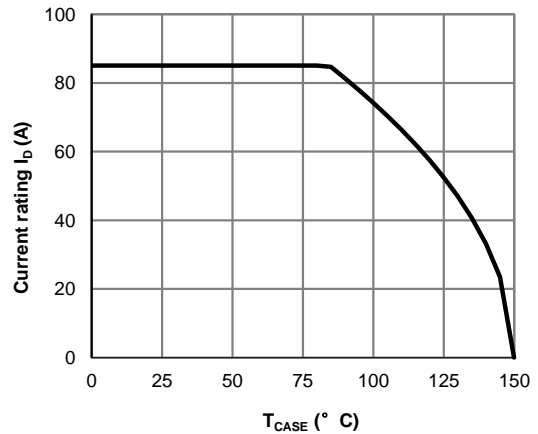


Figure 13: Current De-rating (Note F)

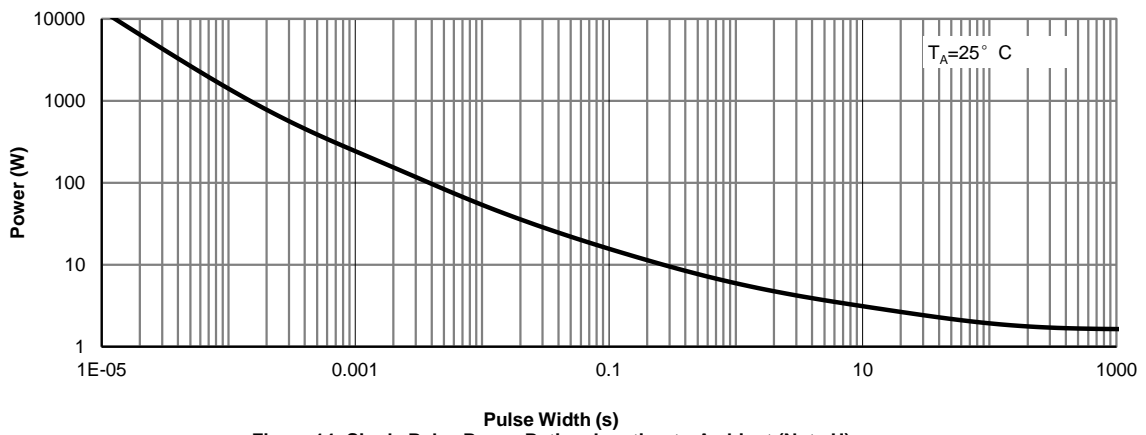


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

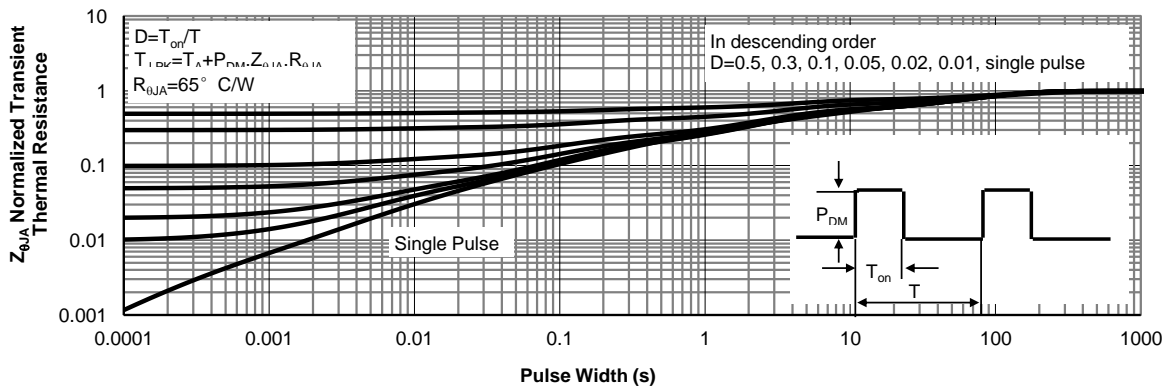


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

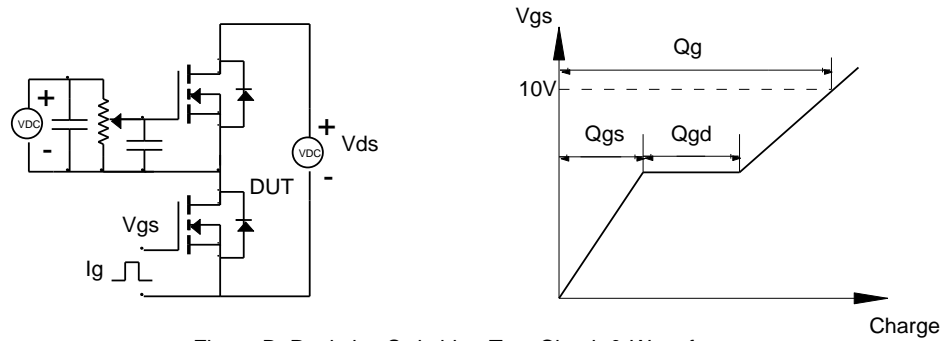


Figure B: Resistive Switching Test Circuit & Waveforms

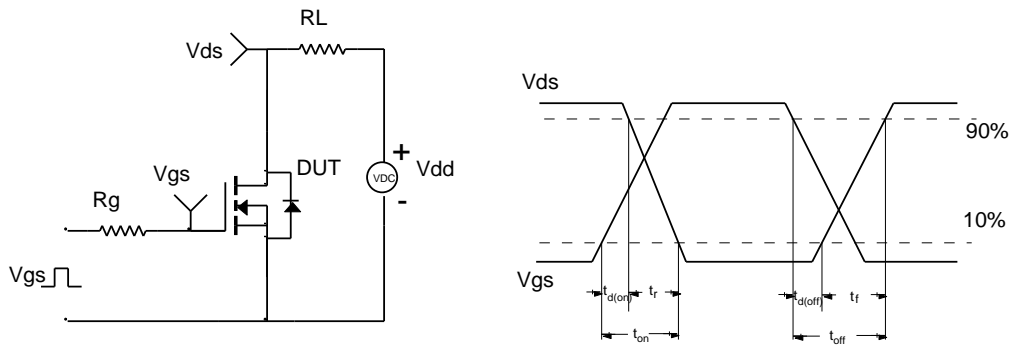


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

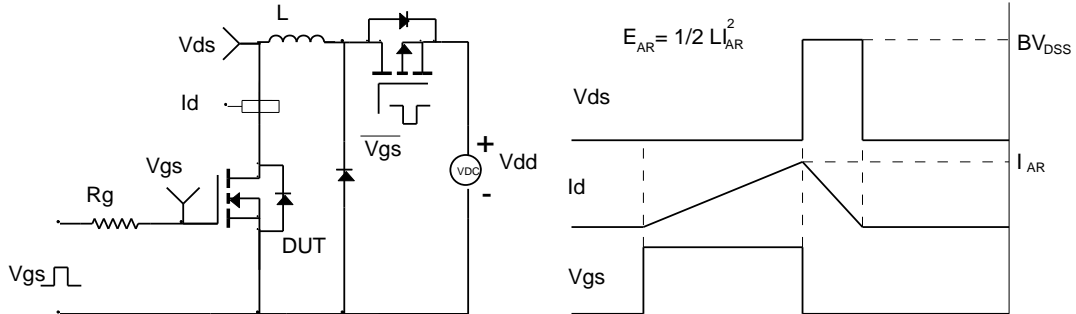
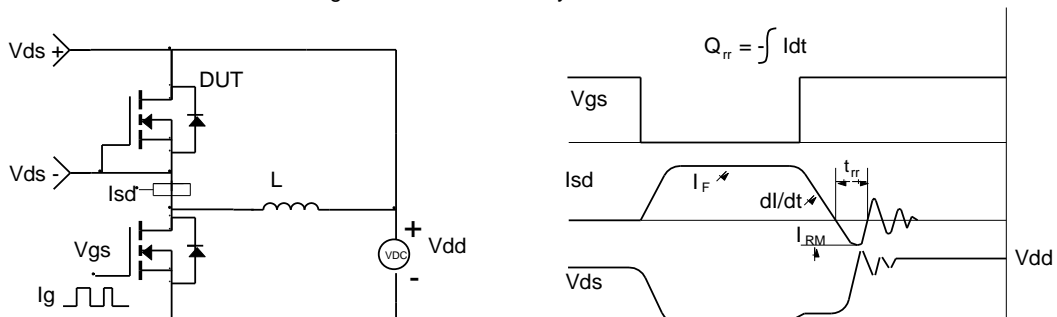


Figure D: Diode Recovery Test Circuit & Waveforms



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